SNx5C3243 符合 RS-232 的 3V 至 5.5V 多通道线路驱动器和接收器

1 特性

- 由 3V 至 5.5V V_{CC} 电源供电
- 始终有效同相接收器输出 (ROUT2B)
- 低待机电流：1 μA（典型值）
- 外部电容器：4 × 0.1 μF
- 接受 5V 逻辑输入及 3.3V 电源
- 可与 SN65C3238、SN75C3238 互操作
- 支持 250kbit/s 至 1Mbit/s 的运行速度
- 使用人体放电模型 (HBM) 时，RS-232 总线引脚 ESD 保护大于 ±15kV

2 应用

- 电池供电型系统
- 个人电子产品
- 笔记本电脑
- 便携式计算机
- 掌上电脑
- 手持设备

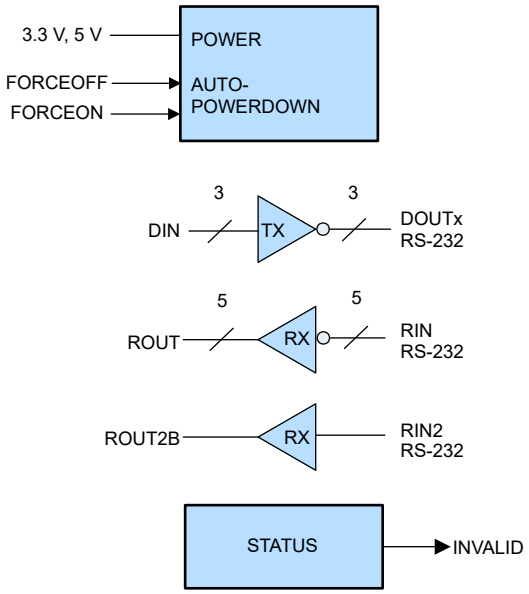
3 说明

SN65C3243 和 SN75C3243 包含三个线路驱动器、五个线路接收器和一个具有引脚对引脚（串行端口连接引脚，包括 GND）±15kV ESD 保护功能的双电荷泵电路。该器件可在异步通信控制器和串行端口连接器之间提供电气接口。电荷泵和四个小型外部电容器支持由 3V 至 5.5V 单电源供电。另外，该器件包括一个始终有效同相输出 (ROUT2B)，这使得使用振铃指示的应用能够在器件断电的情况下发送数据。该器件以高达 1Mbit/s 的数据信号传输速率运行，具有从 24 V/μs 至 150V/μs 的更高压摆率范围。

封装信息

器件型号	封装(1)	封装尺寸（标称值）
SN65C3243 SN75C3243	SSOP (DB)	10.2 mm x 5.30 mm
	SOIC (DW)	17.9 mm x 7.50 mm
	TSSOP (PW)	9.70 mm x 4.40 mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



简化版电路

Table of Contents

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision H (September 2008) to Revision I (October 2022)	Page
• 添加了*器件信息*表、*引脚配置和功能*部分、*ESD 等级*表、*热性能信息*表、*详细说明*部分、*器件和文档支持*部分以及*机械、封装和可订购信息*部分	1
• Changed the I_{CC} Supply current auto-powerdown disabled MAX value from 1 mA to 1.2 mA in the *Electrical Characteristics*	5

5 Pin Configuration and Functions

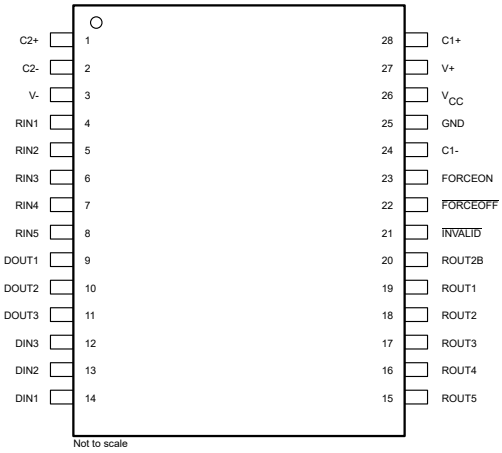


图 5-1. DB, DW, or PW Package, 28 Pin (SSOP, SOIC, TSSOP) (Top View)

表 5-1. Pin Functions

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	C2+	—	Positive terminal of the voltage-doubler charge-pump capacitor
2	C2-	—	Negative terminal of the voltage-doubler charge-pump capacitor
3	V-		Negative charge pump output voltage
4	RIN1	I	RS-232 receiver inputs
5	RIN2		
6	RIN3		
7	RIN4		
8	RIN5		
9	DOUT1	O	RS-232 driver outputs
10	DOUT2		
11	DOUT3		
12	DIN3	I	Driver inputs
13	DIN2		
14	DIN1		
15	ROUT5	O	Receiver outputs
16	ROUT4		
17	ROUT3		
18	ROUT2		
19	ROUT1		
20	ROUT2B	—	Always-active noninverting receiver output;
21	$\overline{\text{INVALID}}$	O	Invalid Output Pin
22	$\overline{\text{FORCEOFF}}$	I	Auto Powerdown Control input (Refer to Truth Table)
23	FORCEON	I	Auto Powerdown Control input (Refer to Truth Table)
24	C1-	—	Negative terminal of the voltage-doubler charge-pump capacitor
25	GND	—	Ground
26	V_{CC}	—	3-V to 5.5-V supply voltage
27	V+	—	Positive charge pump output voltage
28	C1+	—	Positive terminal of the voltage-doubler charge-pump capacitor

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range(2)		–0.3	6	V
V+	Positive-output supply voltage range(2)		–0.3	7	V
V–	Negative-output supply voltage range(2)		0.3	–7	V
V+ – V–	Supply voltage difference(2)			13	V
V_I	Input voltage range	Driver ($\overline{\text{FORCEOFF}}$, FORCEON)	–0.3	6	V
		Receiver	–25	25	
V_O	Output voltage range	Driver	–13.2	13.2	V
T_J	Operating virtual junction temperature			150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network GND.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 on RS-232 bus pins DOUT1/2/3, RIN1/2/3/4/5(1)	±15	kV

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. .

6.3 Recommended Operating Conditions

see 图 7-6 (1)

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{\text{FORCEOFF}}$, FORCEON	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{\text{FORCEOFF}}$, FORCEON				0.8	V
V_I	Driver and control input voltage	DIN, $\overline{\text{FORCEOFF}}$, FORCEON		0		5.5	V
V_I	Receiver input voltage			–25		25	V
T_A	Operating free-air temperature		SN65C3243	–40		85	°C
			SN75C3243	0		70	

(1) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.4 Thermal Information

THERMAL METRIC[1]		DB (SSOP) 28 PINS	DW (SOIC) 28 PINS	PW (TSSOP) 28 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	76.1	59.0	70.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	35.8	28.8	21.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	37.4	30.3	29.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	7.4	7.8	1.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	37.0	30.0	28.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 7-6) [2]

PARAMETER		TEST CONDITIONS		MIN	TYP[1]	MAX	UNIT
I_I	Input leakage current	$\overline{FORCEOFF}$, FORCEON			±0.01	±1	μA
I_{CC}	Supply current	Auto-powerdown disabled	No load, $\overline{FORCEOFF}$ and FORCEON = V_{CC} For DB and PW package		0.3	1.2	mA
		Auto-powerdown disabled	No load, $\overline{FORCEOFF}$ and FORCEON = V_{CC} For DW package		0.3	1	mA
		Powered off	No load, $\overline{FORCEOFF}$ = GND		1	10	μA
		Auto-powerdown enabled	No load, $\overline{FORCEOFF}$ = V_{CC}, FORCEON = GND, All RIN are open or grounded, All DIN are grounded		1	10	

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.6 Electrical Characteristics, Driver Section

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 7-6)

PARAMETER		TEST CONDITIONS[3]			MIN	TYP[1]	MAX	UNIT
V_{OH}	High-level output voltage	All DOUT at R_L = 3 kΩ to GND			5	5.4		V
V_{OL}	Low-level output voltage	All DOUT at R_L = 3 kΩ to GND			–5	–5.4		V
V_O	Output voltage (mouse driveability)	DIN1 = DIN2 = GND, DIN3 = V_{CC}, 3-kΩ to GND at DOUT3, DOUT1 = DOUT2 = 2.5 mA			±5			V
I_{IH}	High-level input current	V_I = V_{CC}				±0.01	±1	μA
I_{IL}	Low-level input current	V_I = GND				±0.01	±1	μA
I_{OS}	Short-circuit output current[2]	V_{CC} = 3.6 V,	V_O = 0 V			±35	±60	mA
		V_{CC} = 5.5 V,	V_O = 0 V			±35	±90	
r_o	Output resistance	V_{CC}, V+, and V– = 0 V,	V_O = ±2 V		300	10M		Ω
I_{off}	Output leakage current	$\overline{FORCEOFF}$ = GND	V_O = ±12 V,	V_{CC} = 3 V to 3.6 V			±25	μA
			V_O = ±10 V,	V_{CC} = 4.5 V to 5.5 V			±25	

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.
(3) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.7 Electrical Characteristics, Receiver Section

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 7-6)

PARAMETER		TEST CONDITIONS(2)	MIN	TYP(1)	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –1 mA	V_{CC} – 0.6	V_{CC} – 0.1		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.6	2.4	V
		V_{CC} = 5 V		1.9	2.4	
V_{IT-}	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.1		V
		V_{CC} = 5 V	0.8	1.4		
V_{hys}	Input hysteresis (V_{IT+} – V_{IT-})			0.5		V
I_{off}	Output leakage current (except ROUT2B)	$\overline{FORCEOFF}$ = 0 V		±0.05	±10	μA
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5	7	kΩ

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.8 Electrical Characteristics, Auto-Powerdown Section

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 7-5)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
$V_{T+(valid)}$	Receiver input threshold for $\overline{INVALID}$ high-level output voltage	FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}		2.7	V
$V_{T-(valid)}$	Receiver input threshold for $\overline{INVALID}$ high-level output voltage	FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}	–2.7		V
$V_{T(invalid)}$	Receiver input threshold for $\overline{INVALID}$ low-level output voltage	FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}	–0.3	0.3	V
V_{OH}	$\overline{INVALID}$ high-level output voltage	I_{OH} = –1 mA, FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}	V_{CC} – 0.6		V
V_{OL}	$\overline{INVALID}$ low-level output voltage	I_{OL} = 1.6 mA, FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}		0.4	V

6.9 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 7-6)

PARAMETER		TEST CONDITIONS(3)			MIN	TYP(1)	MAX	UNIT
	Maximum data rate (see 图 7-1)	R_L = 3 kΩ, One DOUT switching	C_L = 1000 pF		250			kbit/s
			C_L = 250 pF,	V_{CC} = 3 V to 4.5 V	1000			
			C_L = 1000 pF,	V_{CC} = 4.5 V to 5.5 V	1000			
$t_{sk(p)}$	Pulse skew(2)	C_L = 150 pF to 2500 pF,	R_L = 3 kΩ to 7 kΩ,	See 图 7-2		25		ns
SR(tr)	Slew rate, transition region (see 图 7-1)	C_L = 150 pF to 1000 pF,	R_L = 3 kΩ to 7 kΩ,	V_{CC} = 3.3 V	18		150	V/μs

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
(3) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.10 Switching Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS(3)	TYP(1)	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF, See 图 7-3	150	ns
t_{PHL}	Propagation delay time, high- to low-level output	C_L = 150 pF, See 图 7-3	150	ns
t_{en}	Output enable time	C_L = 150 pF, R_L = 3 kΩ, See 图 7-4	200	ns
t_{dis}	Output disable time	C_L = 150 pF, R_L = 3 kΩ, See 图 7-4	200	ns
$t_{sk(p)}$	Pulse skew(2)	See 图 7-3	50	ns

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
(3) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

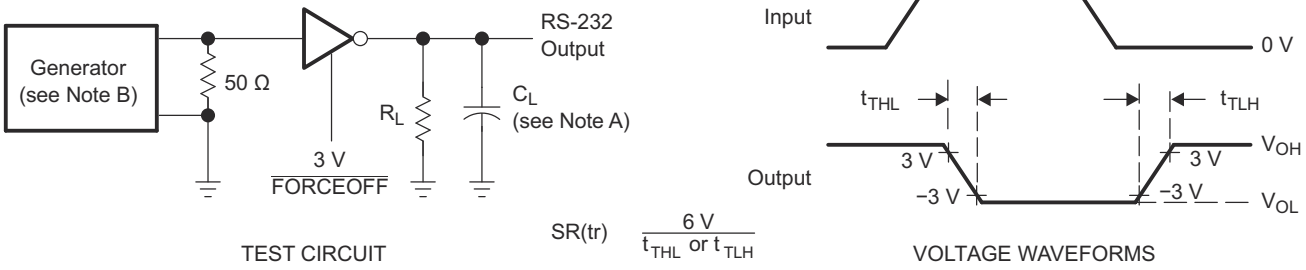
6.11 Switching Characteristics: Auto-Powerdown

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 7-5)

PARAMETER		TYP(1)	UNIT
t_{valid}	Propagation delay time, low- to high-level output	1	μs
$t_{invalid}$	Propagation delay time, high- to low-level output	30	μs
t_{en}	Supply enable time	100	μs

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

7 Parameter Measurement Information

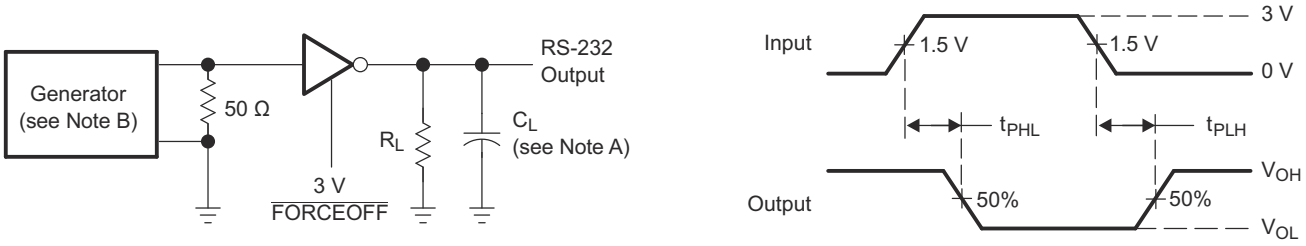


TEST CIRCUIT VOLTAGE WAVEFORMS

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 1 Mbits, Z_O = 50 Ω , 50% duty cycle, t_r ⩽ 10 ns, t_f ⩽ 10 ns.

图 7-1. Driver Slew Rate

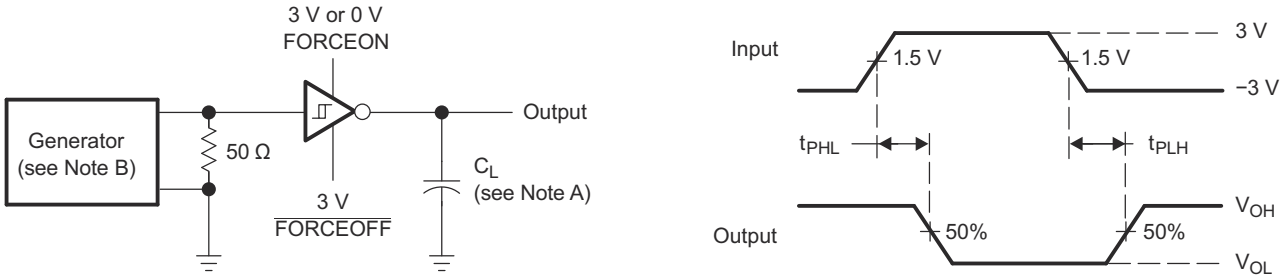


TEST CIRCUIT VOLTAGE WAVEFORMS

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 1 Mbits, Z_O = 50 Ω , 50% duty cycle, t_r ⩽ 10 ns, t_f ⩽ 10 ns.

图 7-2. Driver Pulse Skew

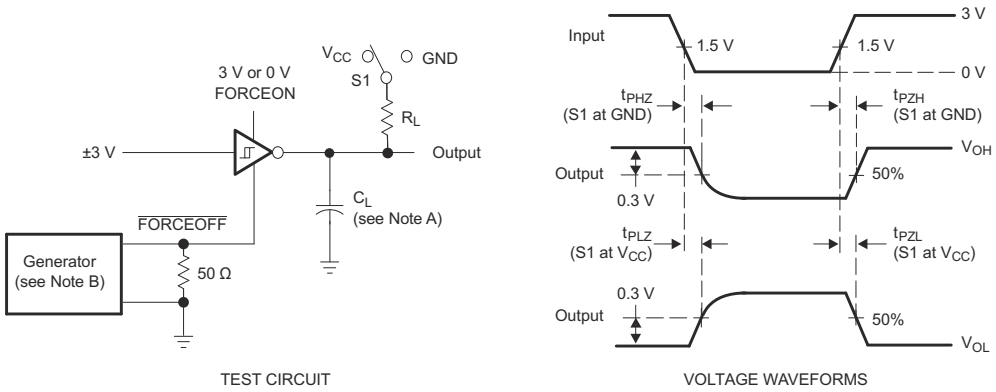


TEST CIRCUIT VOLTAGE WAVEFORMS

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω , 50% duty cycle, t_r ⩽ 10 ns, t_f ⩽ 10 ns.

图 7-3. Receiver Propagation Delay Times



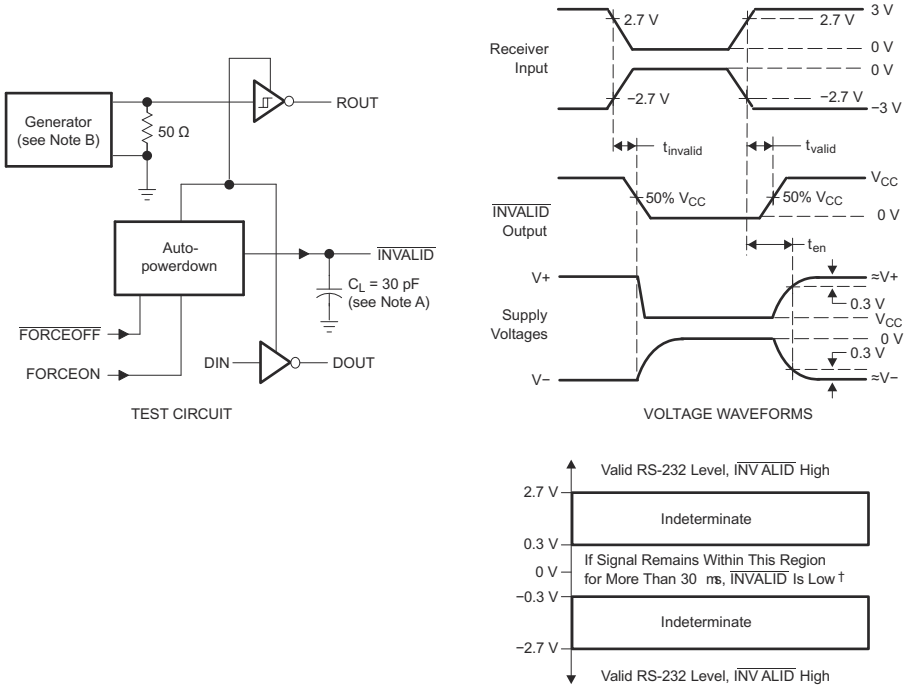
A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω , 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

C. t_{PLZ} and t_{PHZ} are the same as t_{dis}.

D. t_{PZL} and t_{PZH} are the same as t_{en}.

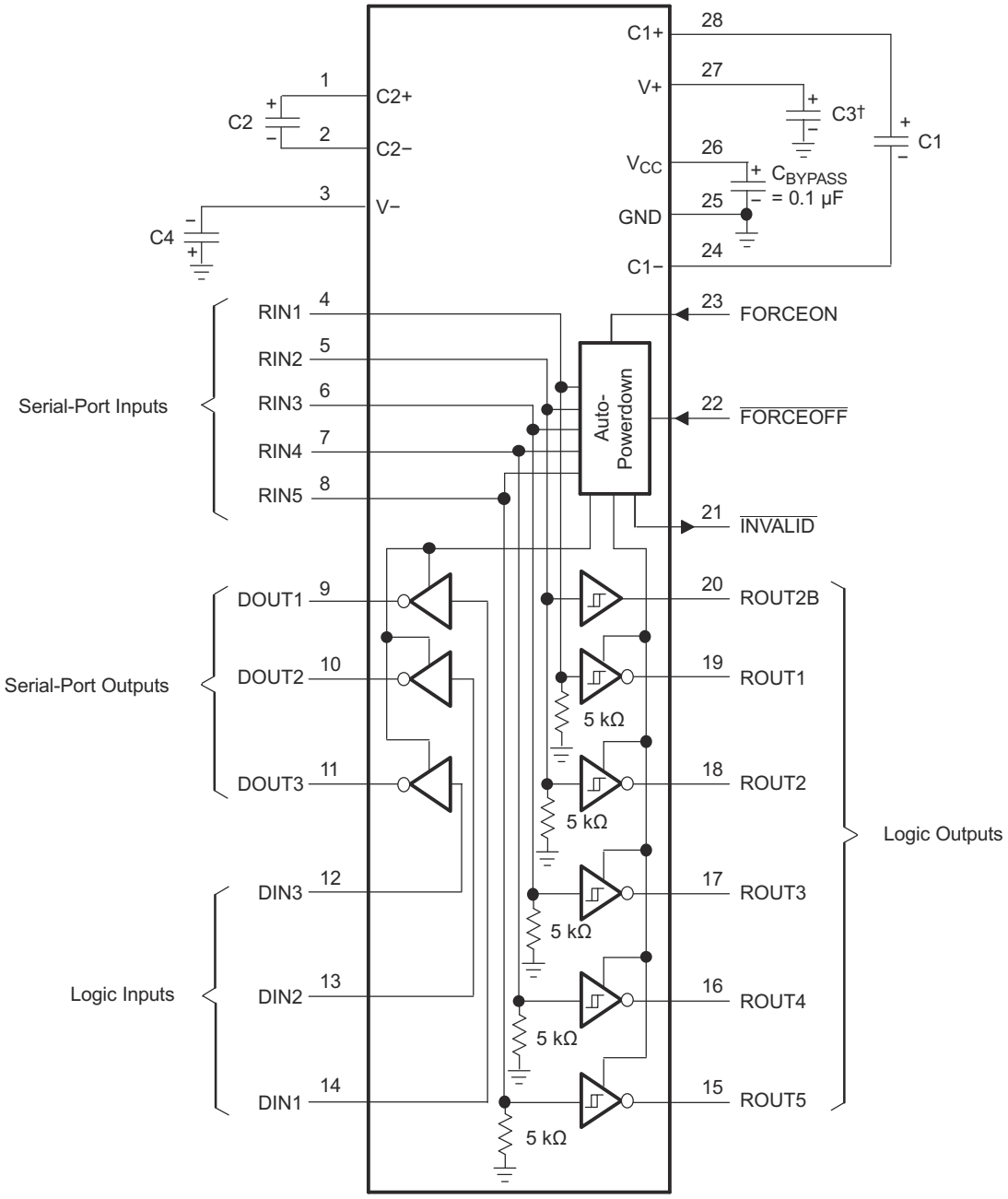
图 7-4. Receiver Enable and Disable Times



A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 5 Mbits, Z_O = 50 Ω , 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

图 7-5. $\overline{\text{INVALID}}$ Propagation Delay Times and Supply Enabling Time



† C3 can be connected to V_{CC} or GND.

A. Resistor values shown are nominal.

图 7-6. Typical Operating Circuit and Capacitor Values

表 7-1. V_{CC} vs Capacitor Values

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.3 V	0.1 µF	0.1 µF
5 V ± 0.5 V	0.047 µF	0.33 µF
3 V to 5.5 V	0.1 µF	0.47 µF

8 Detailed Description

8.1 Overview

Flexible control options for power management are available when the serial port is inactive. The auto-powerdown feature functions when FORCEON is low and $\overline{\text{FORCEOFF}}$ is high. During this mode of operation, if the device does not sense a valid RS-232 signal, the driver outputs are disabled. If $\overline{\text{FORCEOFF}}$ is set low, both drivers and receivers (except ROUT2B) are shut off, and the supply current is reduced to 1 μA. Disconnecting the serial port or turning off the peripheral drivers causes the auto-powerdown condition to occur.

Auto-powerdown can be disabled when FORCEON and $\overline{\text{FORCEOFF}}$ are high and should be done when driving a serial mouse. With auto-powerdown enabled, the device is activated automatically when a valid signal is applied to any receiver input. The $\overline{\text{INVALID}}$ output is used to notify the user if an RS-232 signal is present at any receiver input. $\overline{\text{INVALID}}$ is high (valid data) if any receiver input voltage is greater than 2.7 V or less than –2.7 V or has been between –0.3 V and 0.3 V for less than 30 μs. $\overline{\text{INVALID}}$ is low (invalid data) if all receiver input voltages are between –0.3 V and 0.3 V for more than 30 μs. Refer to 图 7-5 for receiver input levels.

8.2 Device Functional Modes

8.2.1 Function Tables

Each Driver, DIN(1)

INPUTS				OUTPUT DOUT	DRIVER STATUS
DIN	FORCEON	$\overline{\text{FORCEOFF}}$	VALID RIN RS-232 LEVEL		
X	X	L	X	Z	Powered off
L	H	H	X	H	Normal operation with auto-powerdown disabled
H	H	H	X	L	
L	L	H	Yes	H	Normal operation with auto-powerdown enabled
H	L	H	Yes	L	
L	L	H	No	Z	Powered off by auto-powerdown feature
H	L	H	No	Z	

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Each Receiver, RIN(1)

INPUTS				OUTPUTS			RECEIVER STATUS
RIN2	RIN1, RIN3 – RIN5	$\overline{\text{FORCEOFF}}$	VALID RIN RS-232 LEVEL	ROUT2B	ROUT2	ROUT1, ROUT3 – 5	
L	X	L	X	L	Z	Z	Powered off while ROUT2B is active
H	X	L	X	H	Z	Z	
L	L	H	YES	L	H	H	Normal operation with auto-powerdown disabled/enabled
L	H	H	YES	L	L	L	
H	L	H	YES	H	H	H	
H	H	H	YES	H	L	L	
Open	Open	H	YES	L	H	H	

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

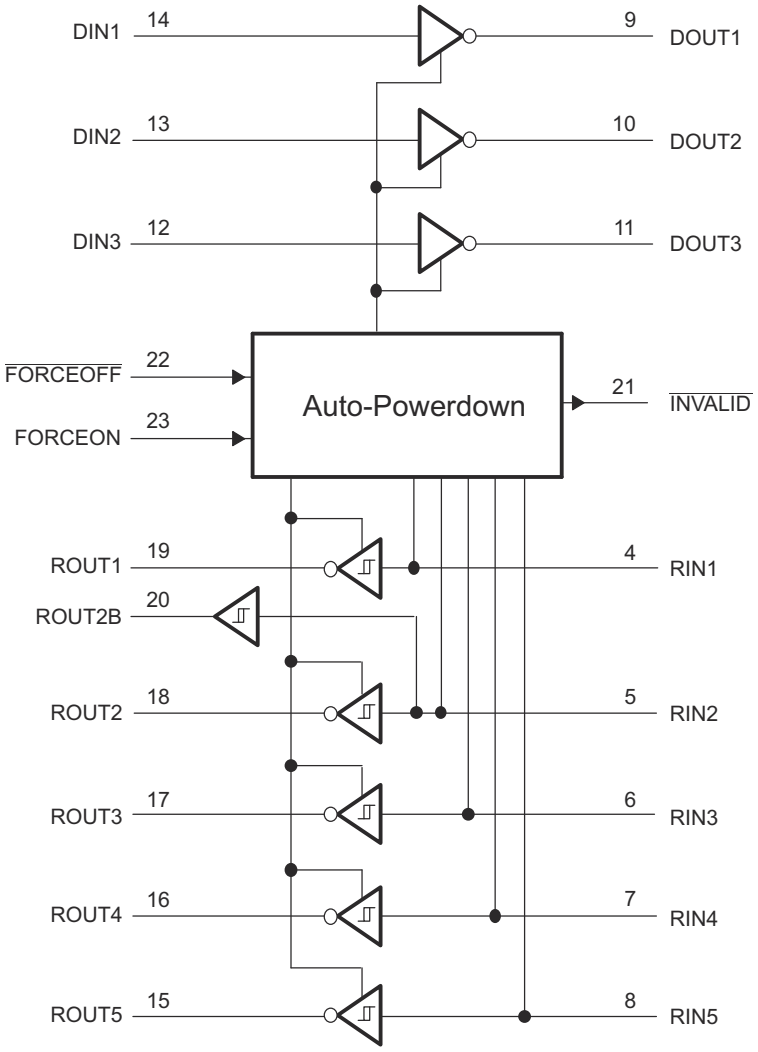


图 8-1. Logic Diagram (Positive Logic)

9 Device and Documentation Support

9.1 Device Support

9.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

9.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

9.4 Trademarks

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9.5 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

9.6 术语表

TI 术语表	本术语表列出并解释了术语、首字母缩略词和定义。

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C3243DBR	ACTIVE	SSOP	DB	28	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3243	Samples
SN65C3243DW	ACTIVE	SOIC	DW	28	20	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3243	Samples
SN65C3243DWR	ACTIVE	SOIC	DW	28	1000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3243	Samples
SN65C3243PW	LIFEBUY	TSSOP	PW	28	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3243	
SN65C3243PWR	ACTIVE	TSSOP	PW	28	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3243	Samples
SN75C3243DBR	ACTIVE	SSOP	DB	28	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3243	Samples
SN75C3243DW	ACTIVE	SOIC	DW	28	20	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3243	Samples
SN75C3243DWR	ACTIVE	SOIC	DW	28	1000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3243	Samples
SN75C3243PW	LIFEBUY	TSSOP	PW	28	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3243	
SN75C3243PWR	ACTIVE	TSSOP	PW	28	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3243	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

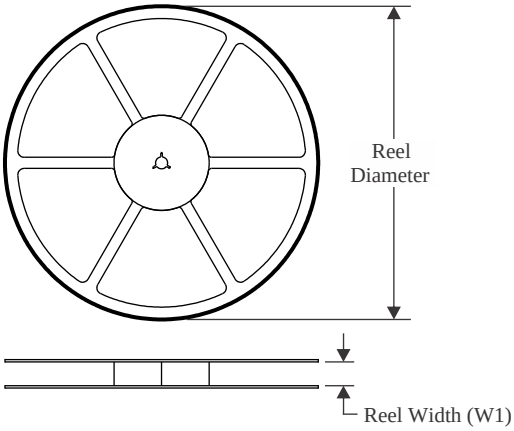
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

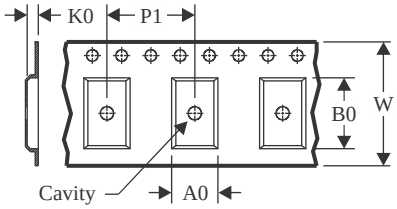
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

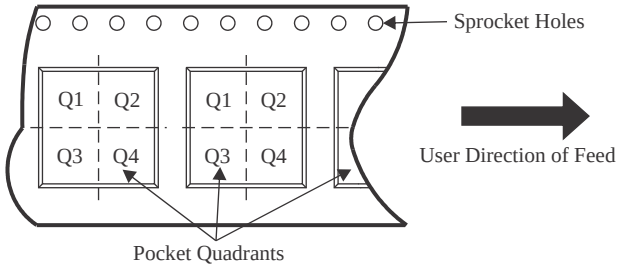


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

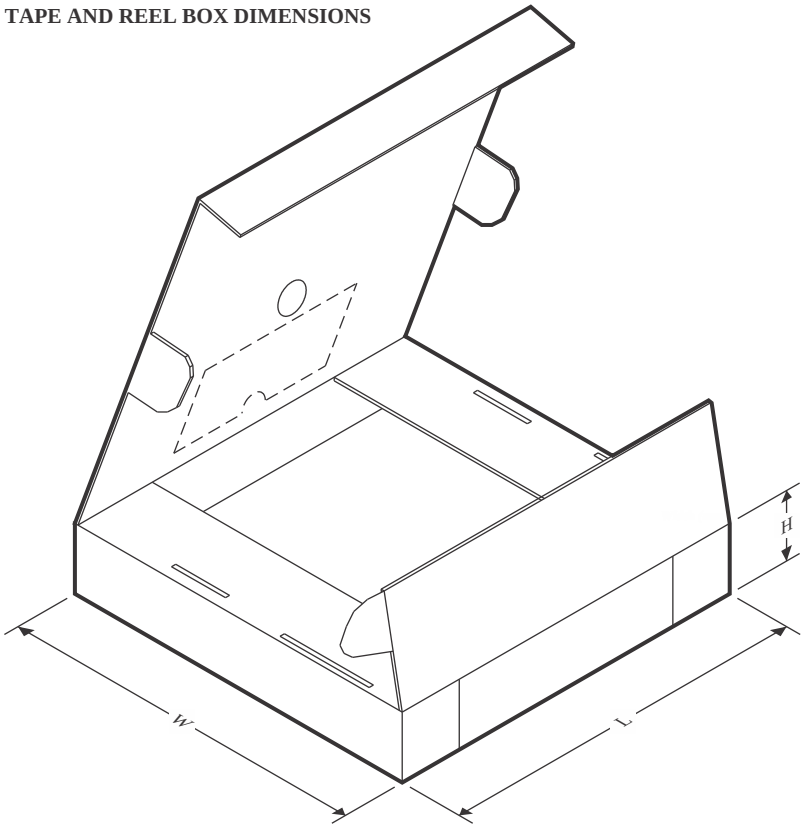
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3243DBR	SSOP	DB	28	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN65C3243DWR	SOIC	DW	28	1000	330.0	32.4	11.35	18.67	3.1	16.0	32.0	Q1
SN65C3243PWR	TSSOP	PW	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1
SN75C3243DBR	SSOP	DB	28	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN75C3243DWR	SOIC	DW	28	1000	330.0	32.4	11.35	18.67	3.1	16.0	32.0	Q1
SN75C3243PWR	TSSOP	PW	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

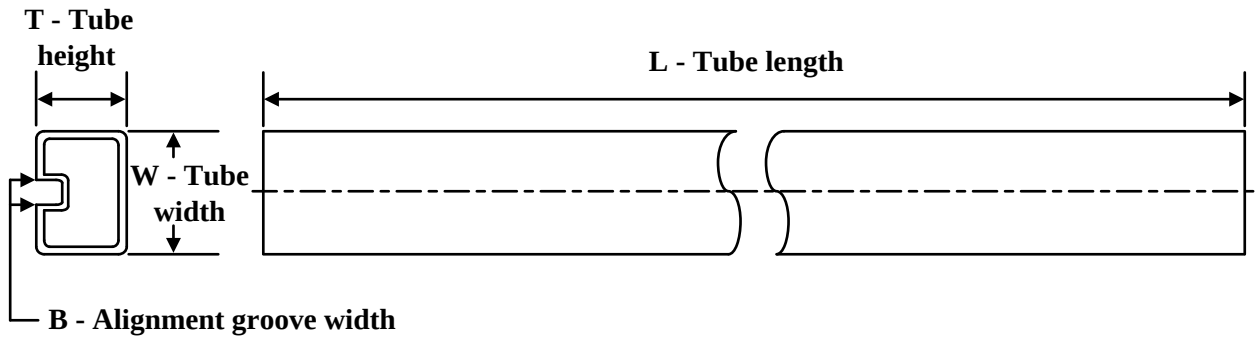
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3243DBR	SSOP	DB	28	2000	356.0	356.0	35.0
SN65C3243DWR	SOIC	DW	28	1000	350.0	350.0	66.0
SN65C3243PWR	TSSOP	PW	28	2000	356.0	356.0	35.0
SN75C3243DBR	SSOP	DB	28	2000	356.0	356.0	35.0
SN75C3243DWR	SOIC	DW	28	1000	350.0	350.0	66.0
SN75C3243PWR	TSSOP	PW	28	2000	356.0	356.0	35.0

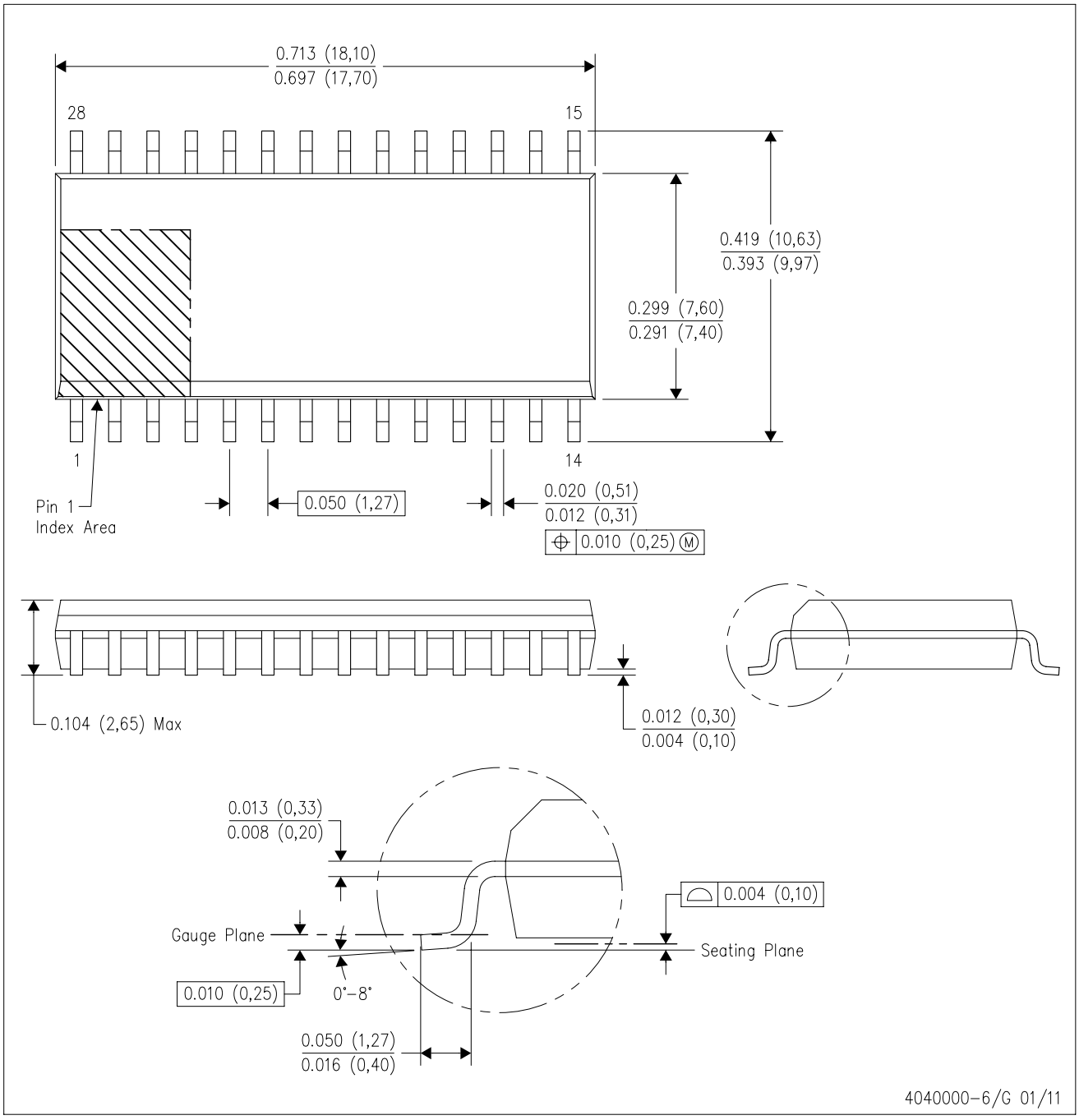
TUBE



*All dimensions are nominal

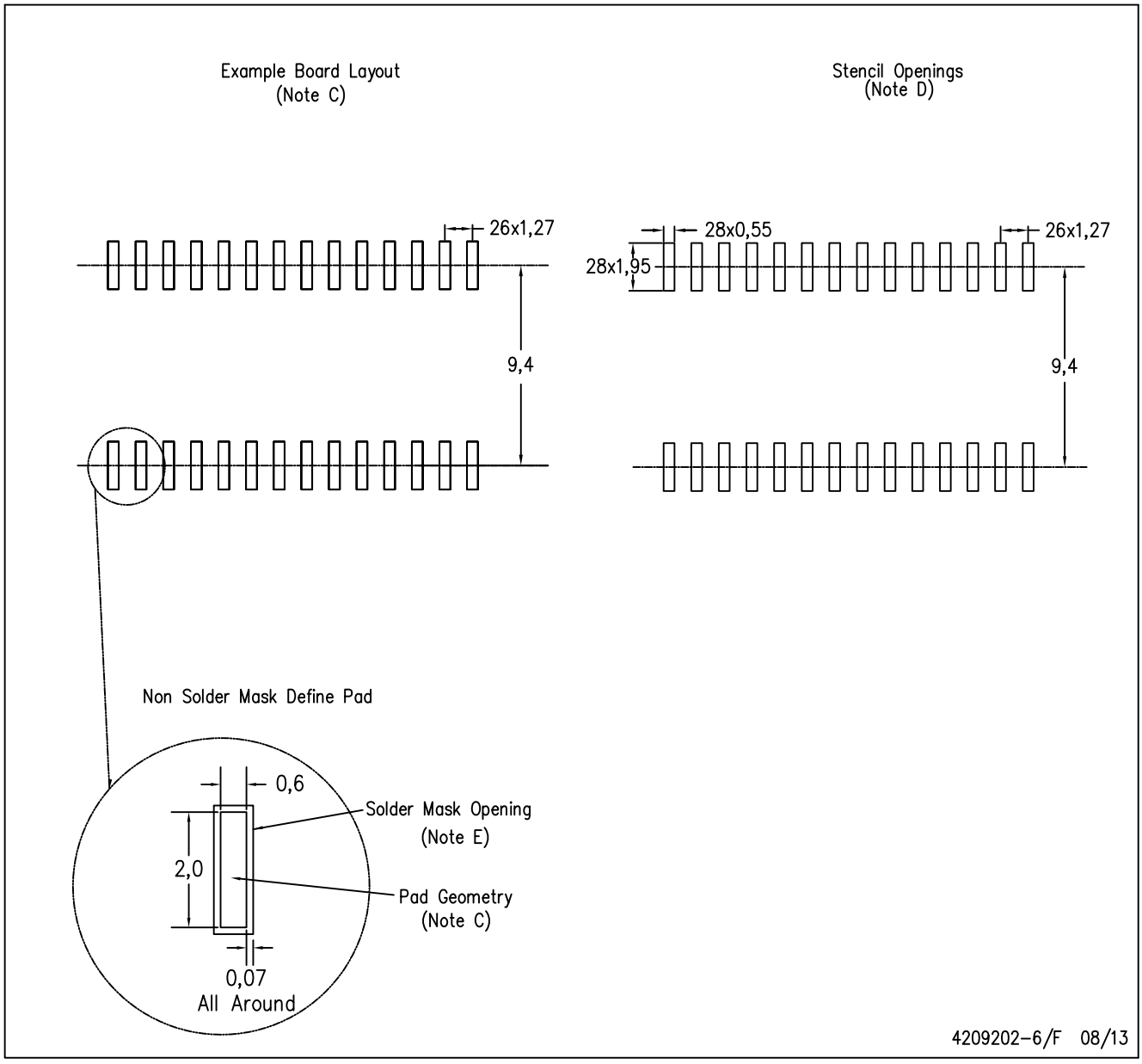
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65C3243DW	DW	SOIC	28	20	506.98	12.7	4826	6.6
SN65C3243PW	PW	TSSOP	28	50	530	10.2	3600	3.5
SN65C3243PW	PW	TSSOP	28	50	530	10.2	3600	3.5
SN75C3243DW	DW	SOIC	28	20	506.98	12.7	4826	6.6
SN75C3243PW	PW	TSSOP	28	50	530	10.2	3600	3.5
SN75C3243PW	PW	TSSOP	28	50	530	10.2	3600	3.5

DW (R–PDSO–G28) PLASTIC SMALL OUTLINE



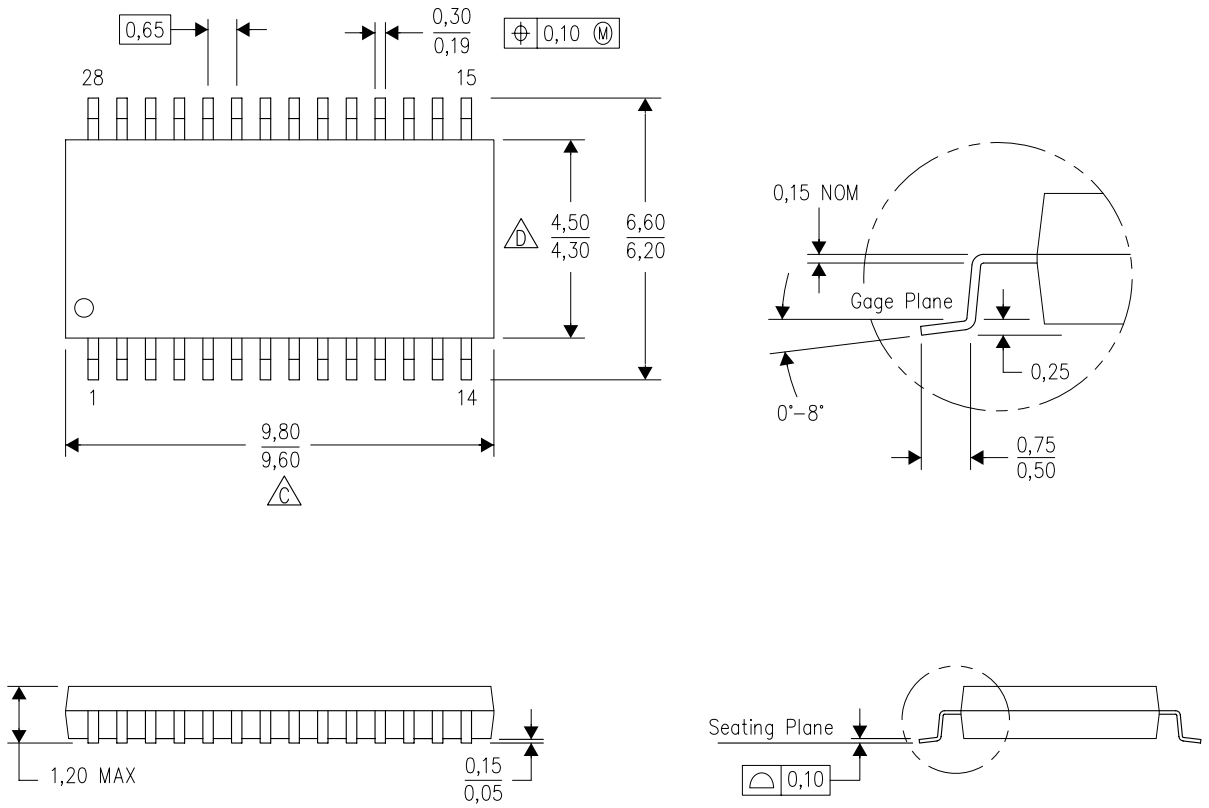
NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AE.

DW (R–PDSO–G28) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Refer to IPC7351 for alternate board design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

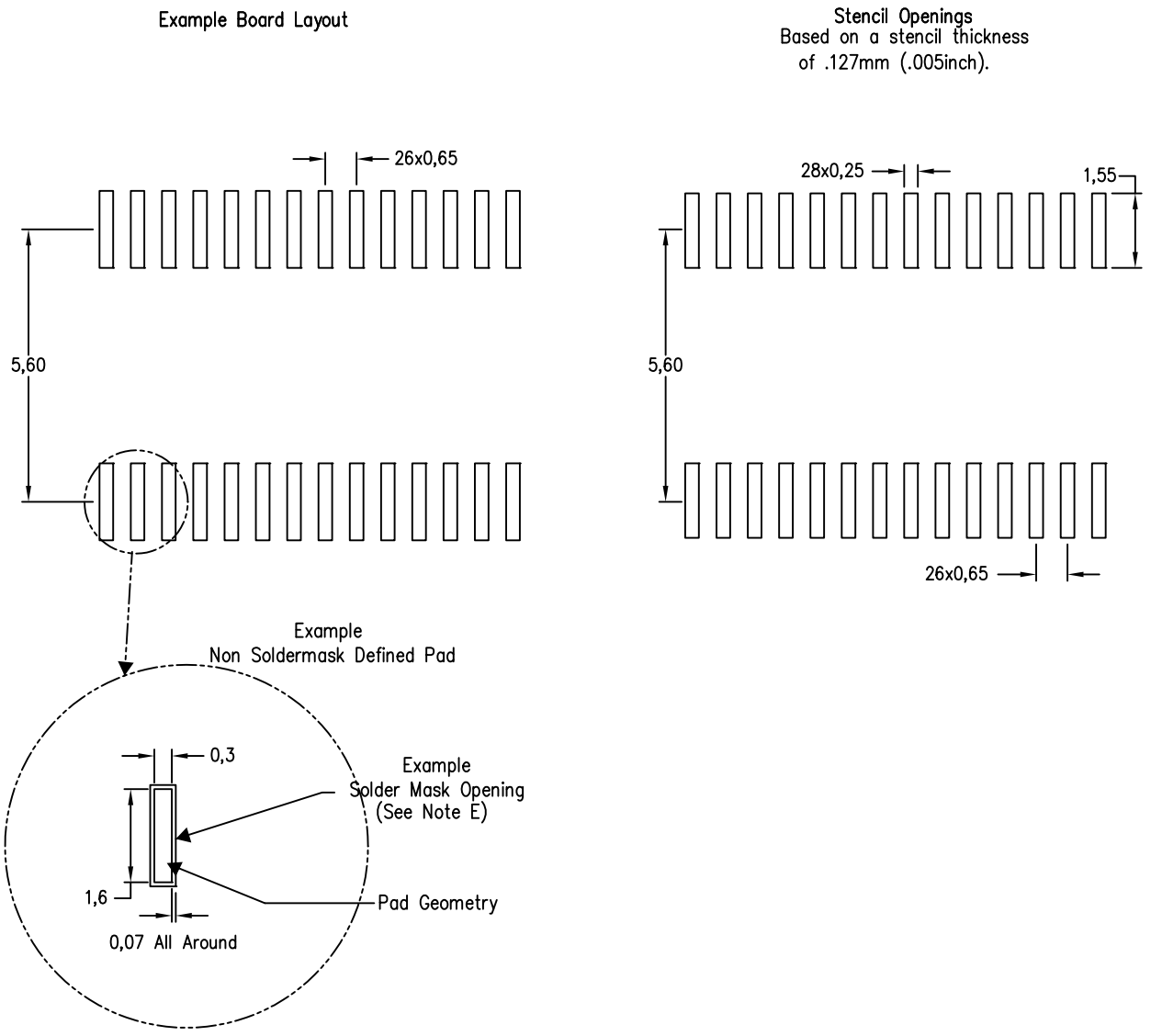
PW (R–PDSO–G28) PLASTIC SMALL OUTLINE



4040064–7/G 02/11

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R–PDSO–G28) PLASTIC SMALL OUTLINE



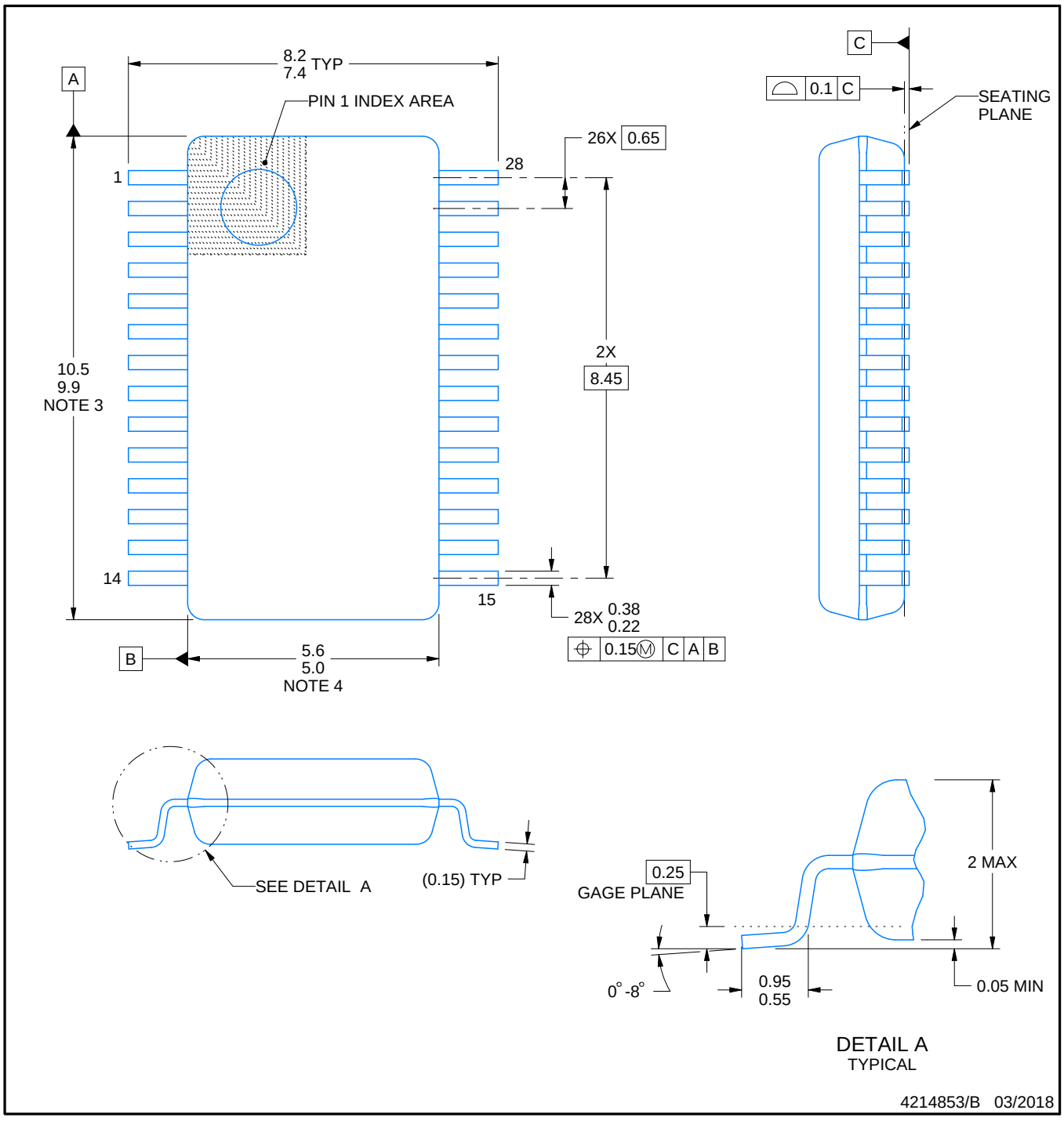
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PACKAGE OUTLINE

DB0028A

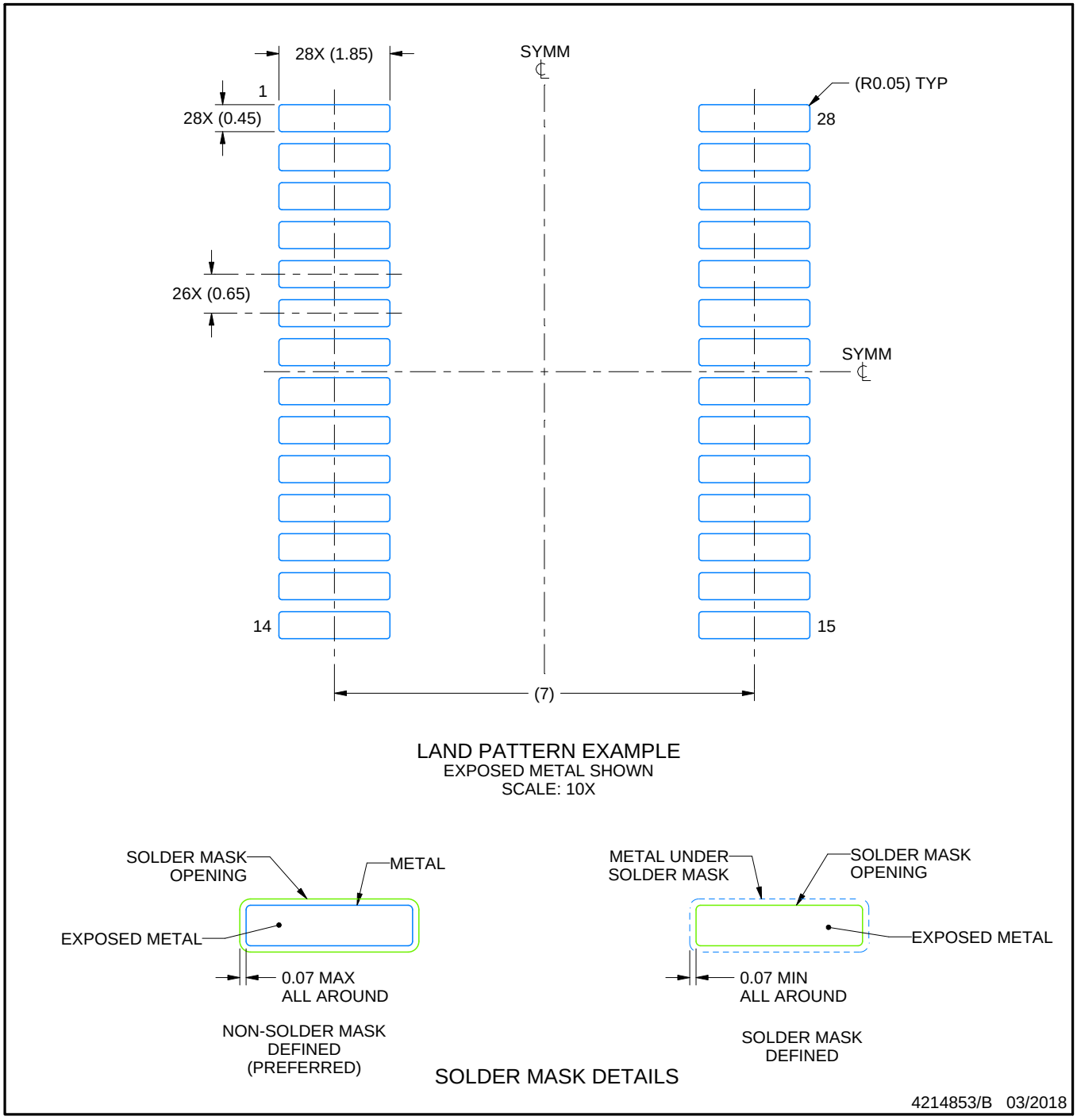
SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



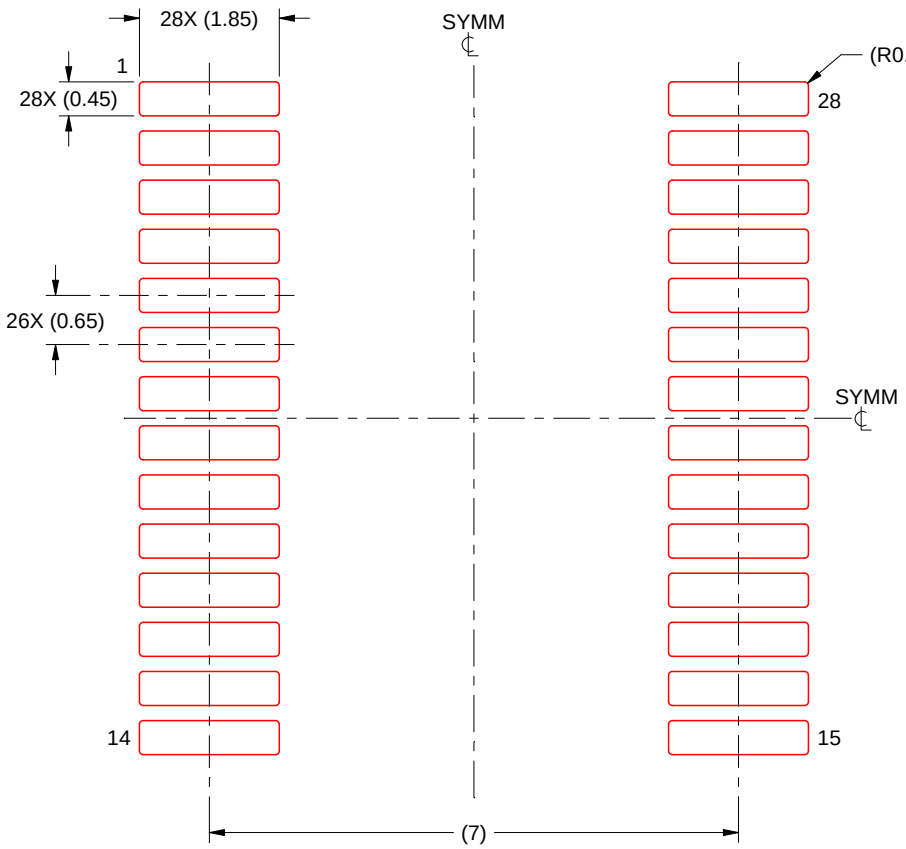
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4214853/B 03/2018

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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